



Shantou Huashan Electronic Devices Co.,Ltd.

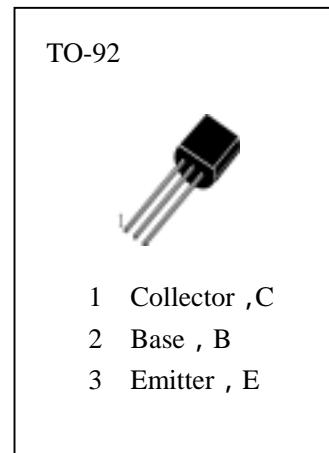
PNP SILICON TRANSISTOR

**H556**

## SWITCHING AND AMPLIFIER

### ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ C$ )

$T_{stg}$ —Storage Temperature.....	-55~150
$T_j$ —Junction Temperature.....	150
$P_C$ —Collector Dissipation.....	500mW
$V_{CBO}$ —Collector-Base Voltage.....	-80V
$V_{CEO}$ —Collector-Emitter Voltage.....	-65V
$V_{EBO}$ —Emitter-Base Voltage.....	-5V
$I_C$ —Collector Current.....	-100mA



### ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ C$ )

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
$I_{CBO}$	Collector Cut-off Current			-15	nA	$V_{CB}=-30V, I_E=0$
$HFE$	DC Current Gain	110		800		$V_{CE}=-5V, I_C=-2mA$
$V_{CE(sat1)}$	Collector- Emitter Saturation Voltage		-90	-300	mV	$I_C=-10mA, I_B=-0.5mA$
$V_{CE(sat2)}$			-250	-650	mV	$I_C=-100mA, I_B=-5mA$
$V_{BE(sat1)}$	Base-Emitter Saturation Voltage		-0. 7		V	$I_C=-10mA, I_B=-0.5mA$
$V_{BE(sat2)}$			-0. 9		V	$I_C=-100mA, I_B=-5mA$
$V_{BE(ON)}$	Base-Emitter On Voltage	-600	-660	-750	mV	$V_{CE}=-5V, I_C=-2mA$
$f_T$	Current Gain-Bandwidth Product		150		MHz	$V_{CE}=-5V, I_C=-10mA$ $f=100MHz$
$NF$	Noise Figure		2	10	dB	$V_{CE}=-5V, I_C=200 \mu A$ $f=1KHz, R_g=2K$

### hfe Classification

A

B

C

110—220

200—450

420—800